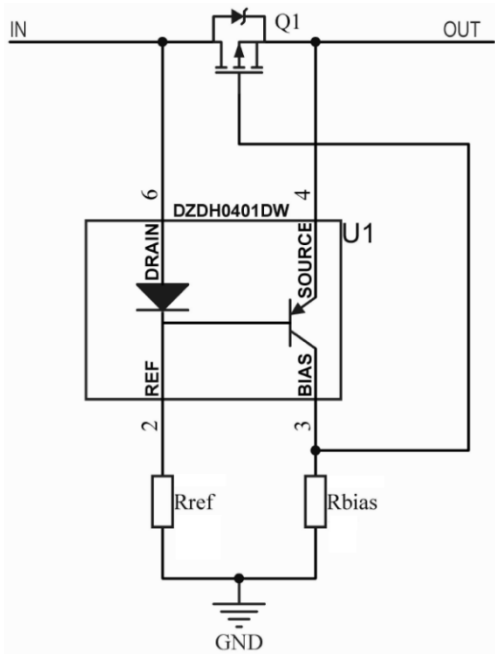


Description

The DZDH0401DW is intended to drive a p-channel enhancement MOSFET configured as an ideal diode. The device operates as a differential amplifier and pMOS controller to minimize forward current losses when $V_{IN} > V_{OUT}$ and provide high isolation when $V_{IN} < V_{OUT}$. The circuit compares the voltage between IN and OUT. If the differential is greater than $\sim 34\text{mV}$ (typ), V_{BIAS} will fall and the pMOS will turn on. If the differential is less than $\sim 34\text{mV}$, V_{BIAS} will rise and the pMOS will turn off, isolating IN from OUT.

Applications

- High-side gate driving pMOS
- High-side disconnect switches
- Battery discharge protections
- Emergency lighting
- Active ORing redundant power supplies



Typical Configuration

Features

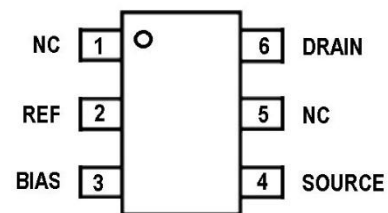
- Max Input Voltage: 40V
- Peak Bias Current: -300mA
- Max Reverse Voltage Protection: 50V
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative.**
<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

- Package: SOT363
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Finish. Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (Approximate)



SOT363 Top View



Pinout

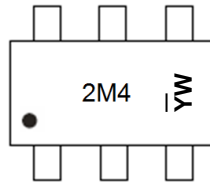
Ordering Information (Note 4)

Orderable Part Number	Package	Marking	Reel Size (inches)	Tape Width (mm)	Packing	
					Qty.	Carrier
DZDH0401DW-7	SOT363	2M4	7	8	3,000	Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

SOT363



2M4 = Product Type Marking Code
 YW = Date Code Marking
 Y = Year: 0 to 9 (ex: 6 = 2026)
 W = Week: A to Z: Week 1 to 26;
 a to z: Week 27 to 52; z Represents
 Week 52 and 53

Date Code Key

Year	2020	-	2026	2027	2028	2029	2030	2031	2032	2033	2034	2035
Code	H	-	N	P	R	S	T	U	V	W	X	Y

Week	1-26	27-52	53
Code	A-Z	a-z	z

Absolute Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

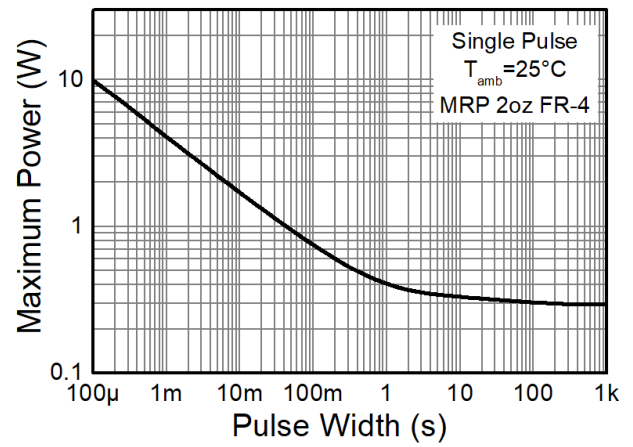
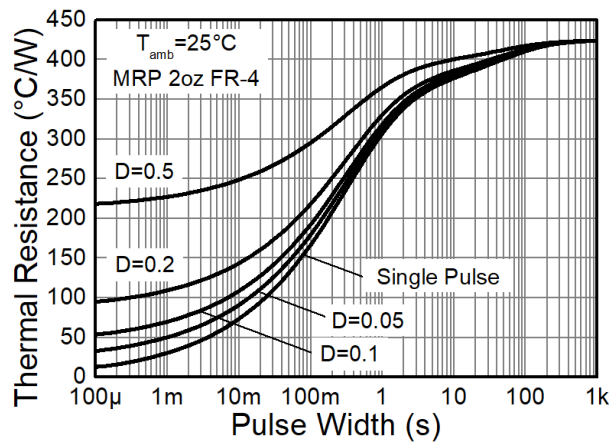
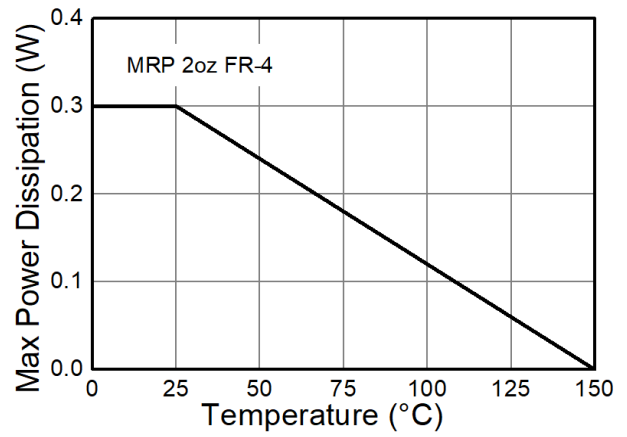
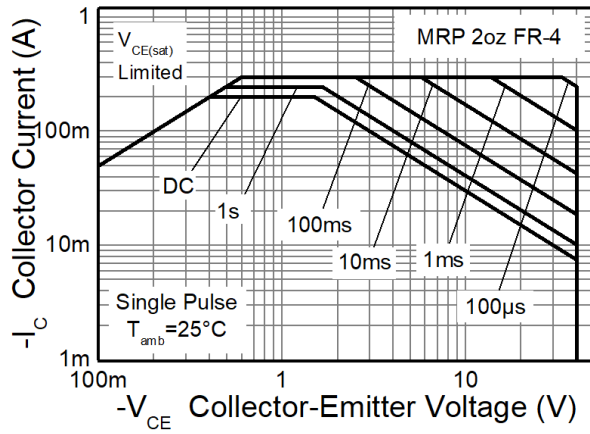
Characteristic	Symbol	Value	Unit
DRAIN BIAS Voltage	V _{DRAIN-BIAS}	40	V
SOURCE DRAIN Voltage	V _{SOURCE-DRAIN}	50	V
BIAS Current	I _{BIAS}	-300	mA
DRAIN Current	I _{DRAIN}	300	mA

Thermal Characteristics – Total Device (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	300	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	424	°C/W
Thermal Resistance, Junction to Case (Note 5)	R _{θJC}	111	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C

Note: 5. For a device mounted on minimum recommended pad layout with 1oz copper that is on a single-sided 1.6mm FR4 PCB; the device is measured under still air conditions whilst operating in a steady state.

Thermal Characteristics – Total Device



Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
DRAIN-BIAS Voltage	$V_{\text{DRAIN-BIAS}}$	40	78	—	V	$I_{\text{DRAIN}} = 100\mu\text{A}$
SOURCE-DRAIN Voltage	$V_{\text{SOURCE-DRAIN}}$	50	84	—	V	$I_{\text{SOURCE}} = 100\mu\text{A}$
DRAIN-REF Voltage	$V_{\text{DRAIN-REF}}$	—	588	—	mV	$I_{\text{DRAIN}} = 100\mu\text{A}$
SOURCE Current	I_{SOURCE}	—	11.6	—	μA	$V_{\text{SOURCE-REF}} = 0.56\text{V}$
REF-SOURCE Voltage	$V_{\text{REF-SOURCE}}$	—	-554	—	mV	$I_{\text{REF}} = -10\mu\text{A}$
Turn-Off Differential Voltage	V_T	5	34	80	mV	$I_{\text{DRAIN}} = 100\mu\text{A}; I_{\text{SOURCE}} = 10\mu\text{A}$
REF-SOURCE Voltage ($V_{\text{BIAS low}}$)	$V_{\text{REF-SOURCE}}$	-250	-472	—	mV	$V_{\text{BIAS-SOURCE}} = -5\text{V}; I_{\text{BIAS}} = -1\mu\text{A}$
		-300	-541	—	mV	$V_{\text{BIAS-SOURCE}} = -5\text{V}; I_{\text{BIAS}} = -10\mu\text{A}$
REF-SOURCE Voltage ($V_{\text{BIAS high}}$)	$V_{\text{REF-SOURCE}}$	—	-601	-800	mV	$V_{\text{BIAS-SOURCE}} = -0.5\text{V}; I_{\text{BIAS}} = -100\mu\text{A}$
		—	-663	-850	mV	$V_{\text{BIAS-SOURCE}} = -0.5\text{V}; I_{\text{BIAS}} = -1\text{mA}$

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

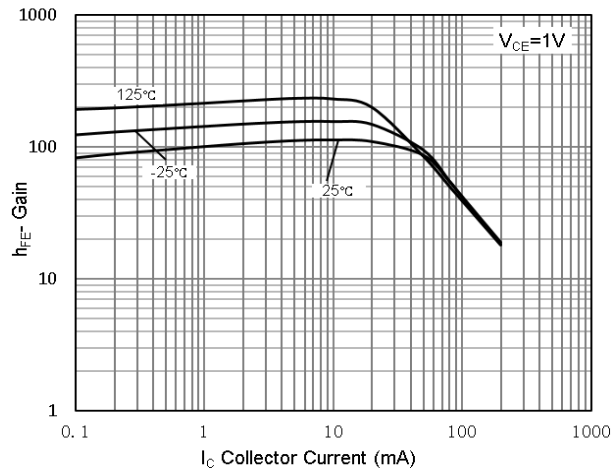


Fig.5 h_{FE} vs I_C

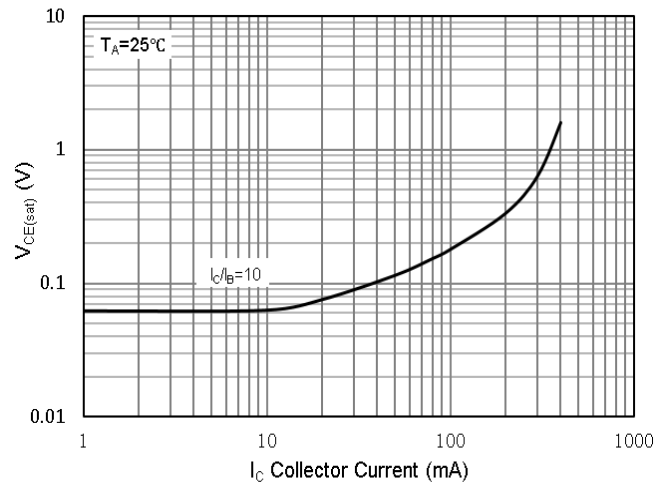


Fig.6 $V_{CE(sat)}$ vs I_C

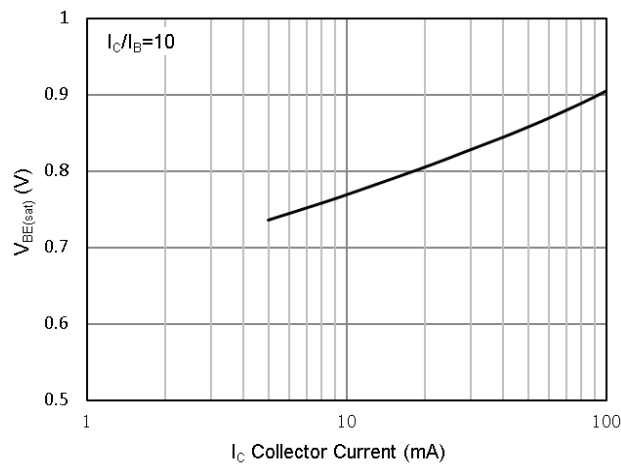


Fig.7 $V_{BE(sat)}$ vs I_C

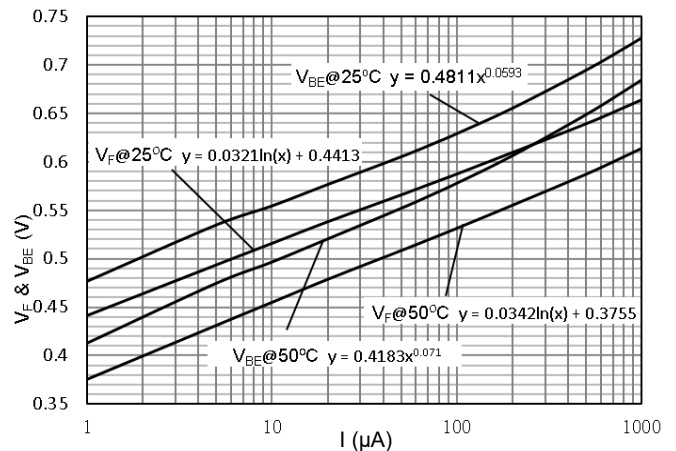
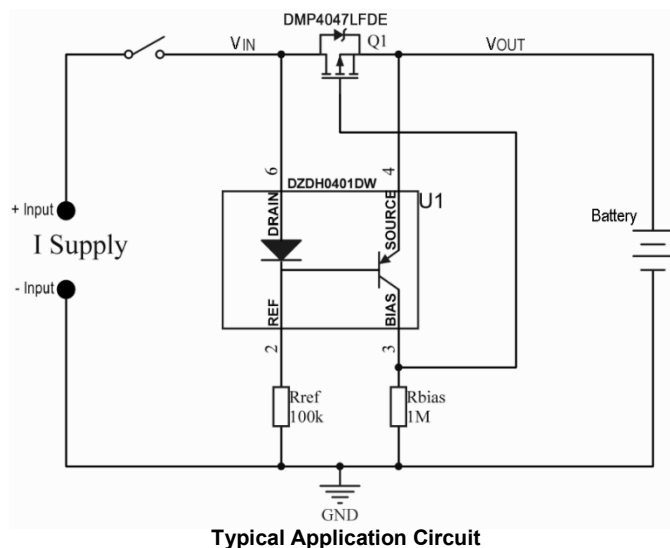


Fig.8 I vs V_F & V_{BE}

Typical Application Circuit / Pinout Details / Functional Description



Pin	Name	Function
1	NC	No internal connection
2	REF	Reference current to set V_F
3	BIAS	Reference current to set V_{BE} and control Gate
4	SOURCE	V_{OUT} sense voltage
5	NC	No internal connection
6	DRAIN	V_{IN} sense voltage
n/a	Rref	This resistor sets the turn-off speed of the FET. The lower the resistance, the more base drive to the transistor, the faster the transistor shorts out the gate to turn off the FET.
n/a	Rbias	This resistor sets the turn-on speed of the FET. When the ideal diode circuit is turning on, the PNP is held off by the diode and FET voltage drops. It is Rbias that pulls the gate low and turns on the FET.
n/a	Rbias : Rref	Ideal diode Turn-Off threshold voltage $V_T \propto R_{bias} / R_{ref}$
n/a	Vref	Voltage across Rref

Functional Description (Refer to Typical Application Circuit above)

Supply Connect

As a +Input is applied, the body drain diode of Q1 becomes forward biased. U1 diode holds U1 transistor base at $V_{IN} - V_F$, and so V_{BE} is too low to turn on U1 transistor. As Q1 gate capacitance charges through Rbias, Q1 turns on and R_{DS} decreases causing V_{DS} to decrease and V_{BE} to increase until U1 transistor starts to conduct. This process continues until Q1 R_{DS} reaches its minimum value and U1 transistor V_{BE} cannot increase and I_C reaches its maximum. V_{GS} should be high enough at this point to ensure linear operation.

Rref and Rbias set the currents through U1 diode and U1 collector respectively so that $V_{F(DIODE)}$ is greater than $V_{BE(on)}$.

Supply Disconnect

As the +Input is removed, $V_{DS} < V_T$, Q1 is on and $V_{IN} = V_{OUT}$, causing V_{REF} to fall and U1 $V_{BE} > V_{BE(on)}$ so U1 transistor discharges Q1 gate capacitance and Q1 turns off causing V_{IN} to fall to 0V.

Quiescent Current and Isolation

With a battery connected at Supply Out, there are two leakage paths back to the Supply In. One is straight through Q1 and the other is through U1 emitter-anode. The high reverse breakdown voltage of U1 diode provides a high isolation path. The Rref & Rbias currents bias U1 transistor on which keeps Q1 off. These resistors' values are chosen to minimize quiescent current operation of the circuit.

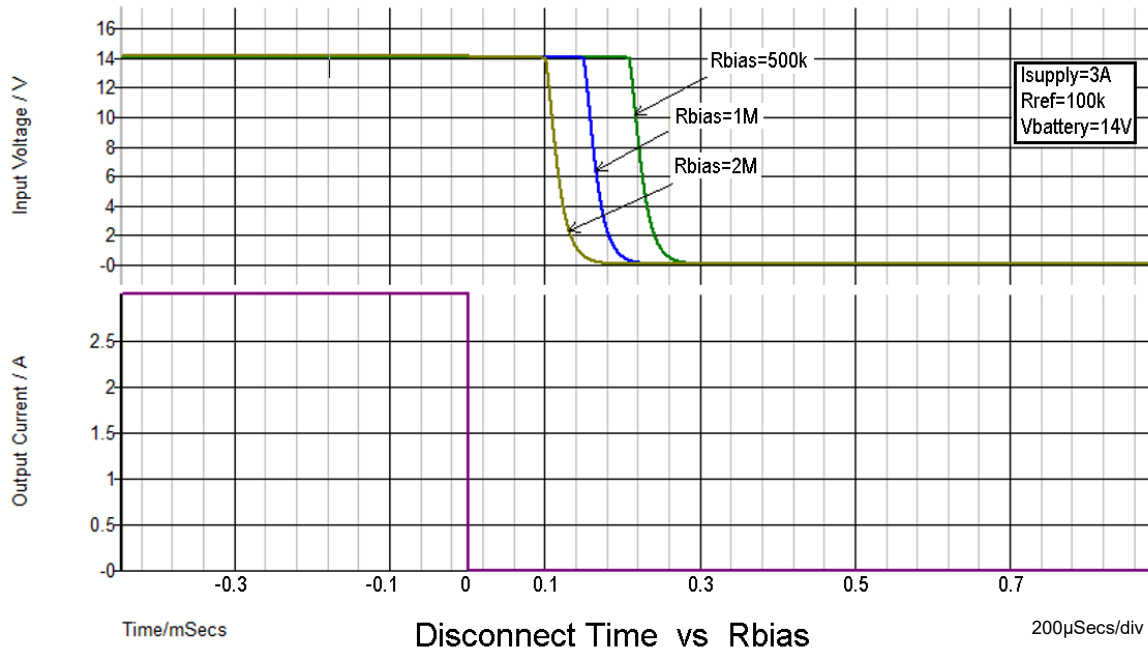
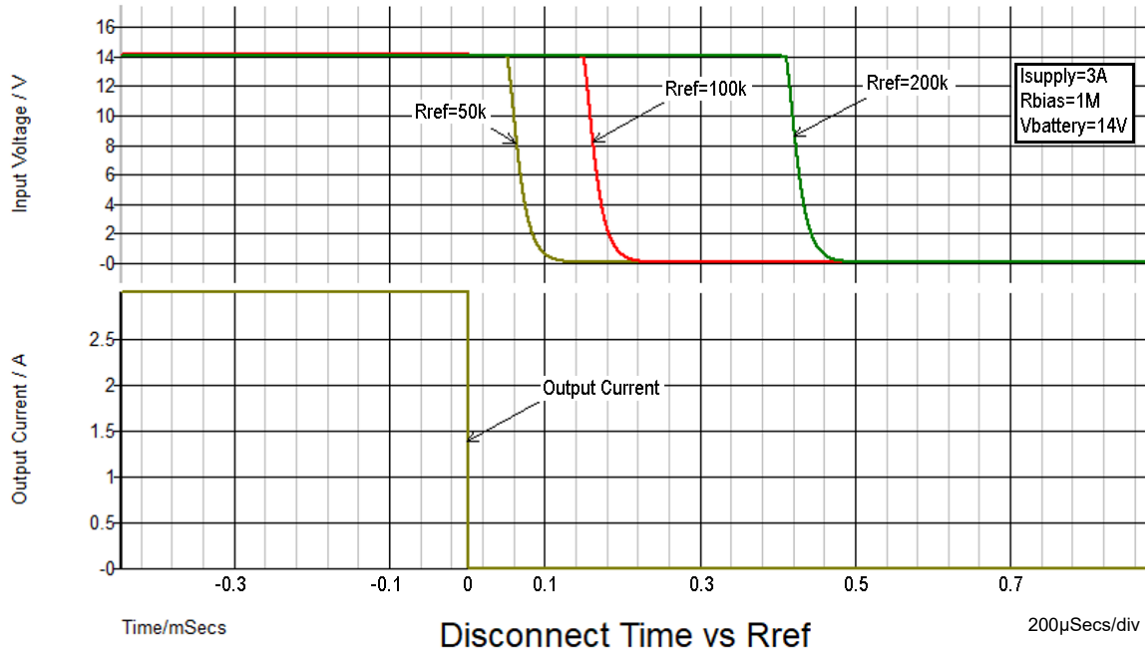
Typical Charging Conditions ($T_A = +25^\circ\text{C}$, $V_{BATT} = 14\text{V}$, switch closed, $I_{SUPPLY} = 3\text{A}$)			
Parameter	Symbol	Typ	Unit
Input Voltage	V_{IN}	14.1	V
Input Current	I_{IN}	3	A
Output Voltage	V_{OUT}	14	V
Output Current	I_{OUT}	3.0	A
Diode Forward Voltage	V_F	0.6	V
Diode forward Current	I_F	135	μA
Reference Voltage	V_{REF}	13.4	V
Reference Current	I_{REF}	136.6	μA
Base Current	I_B	1.6	μA
Emitter Current	I_E	12.1	μA
Bias Voltage	V_{BIAS}	10.5	V
Collector Current	I_C	10.5	μA
Operating Current	I_{CC}	147	μA

Typical Non-Charging Conditions ($T_A = +25^\circ\text{C}$, $V_{BATT} = 14\text{V}$, switch open, $I_{SUPPLY} = 3\text{A}$)			
Parameter	Symbol	Typ	Unit
Input Voltage	V_{IN}	—	μV
Input Current	I_{IN}	—	A
Output Voltage	V_{OUT}	14	V
Output Current	I_{OUT}	—	A
Diode Forward Voltage	V_F	—	V
Diode forward current	I_F	0	μA
Reference Voltage	V_{REF}	13.3	V
Reference Current	I_{REF}	133	μA
Base Current	I_B	133	μA
Emitter Current	I_E	145	μA
Bias Voltage	V_{BIAS}	13.94	V
Bias Current	I_{BIAS}	13.94	μA
Operating Current	I_{CC}	147	μA

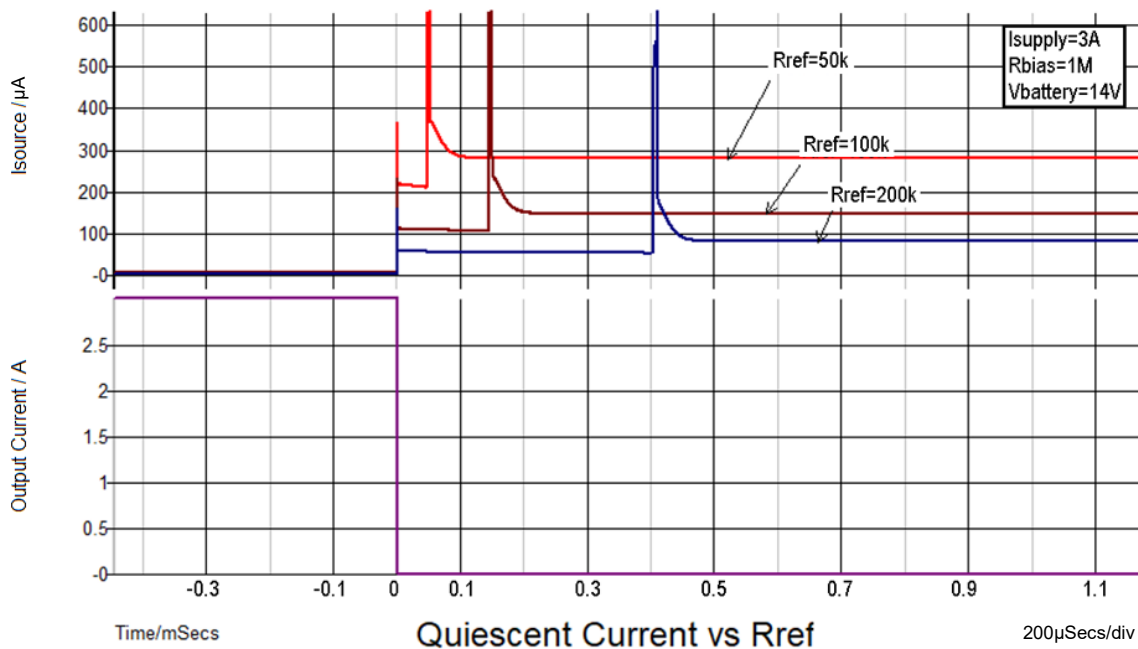
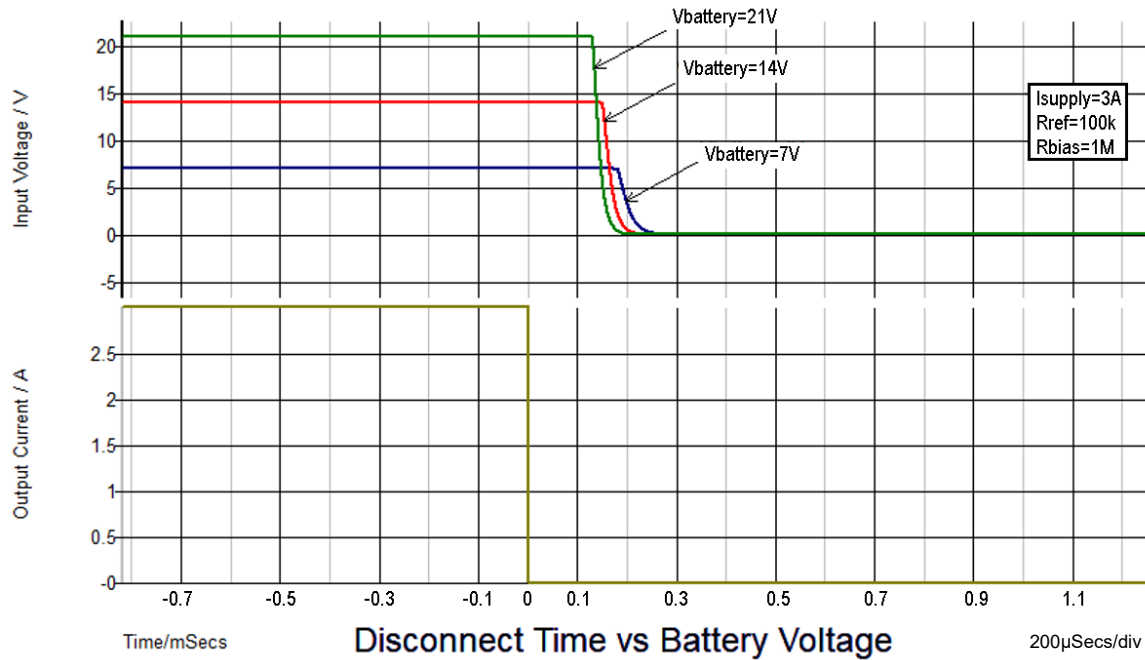
Typical Application Circuit / Pinout Details / Functional Description (continued)

Timing

Switching speed is affected by pMOS characteristics, R_{bias} , R_{ref} , and operating voltage. Using the typical application circuit, we can see how modifying values can affect the timing in the simulations below.



Typical Application Circuit / Pinout Details / Functional Description (continued)



Typical Application Circuit / Pinout Details / Functional Description (continued)

Ideal Diode Power Saving

The typical voltage drop across a standard diode rectifier means higher power dissipation and more heat to manage. This both wastes power and significantly drops the potential on low voltage rails.

Example:

A diode rectifier with a typical forward voltage $V_F = 0.55V$ carrying 3A current would dissipate 1.65W ($I \times V_F$).

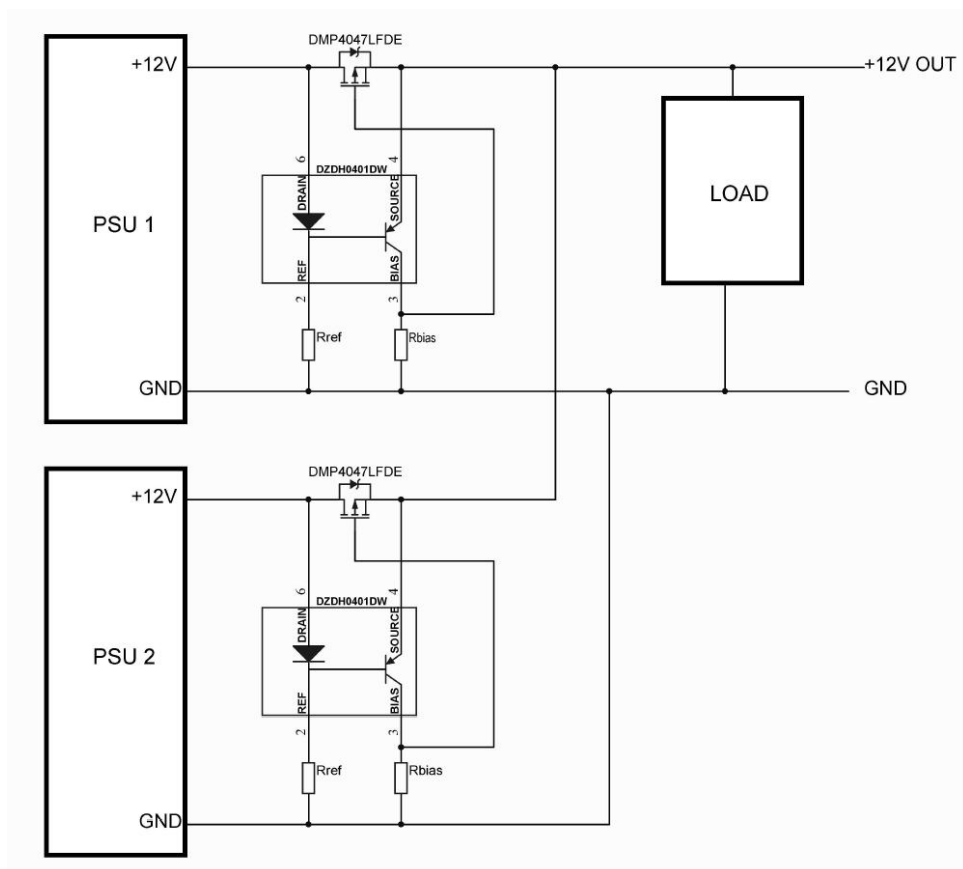
Whereas with pMOSFET such as the DMP4047LFDE that has an $R_{DS(ON)}$ of 33m Ω , the power dissipation reduces to only 0.29W ($I^2 \times R$).

Hence, very low $R_{DS(ON)}$ Power MOSFETs can replace the standard rectifiers and the DZDH0401DW controls the MOSFET as an ideal diode.

N+1 Redundancy ORing Controller

Critical systems require a fault-tolerant power supply that can be achieved by paralleling two or more PSUs into an (N+1) redundancy configuration.

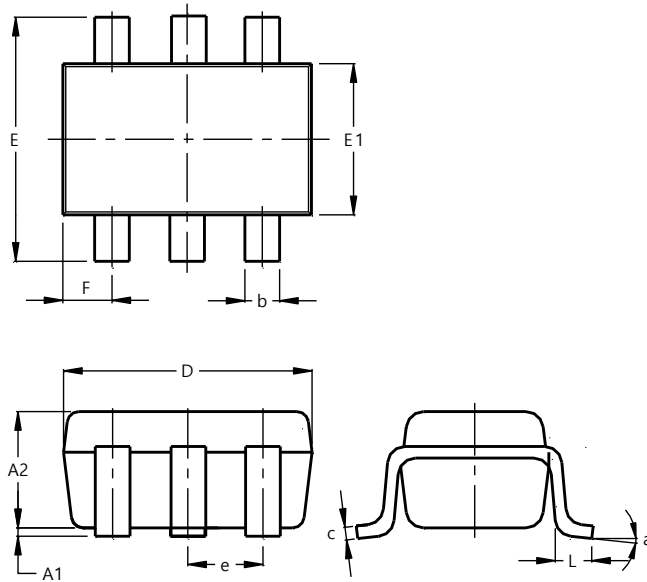
During normal operation, usually all PSUs equally share the load for maximum reliability. If one of the PSUs is unplugged or fails, then the other PSUs fully support the load. To avoid the faulty PSU from affecting the common bus, an ORing rectifier blocks the reverse current flow into the faulty PSU. Likewise, during hot swap, the ORing rectifiers isolate a PSU's discharged output capacitors from the common bus.



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT363

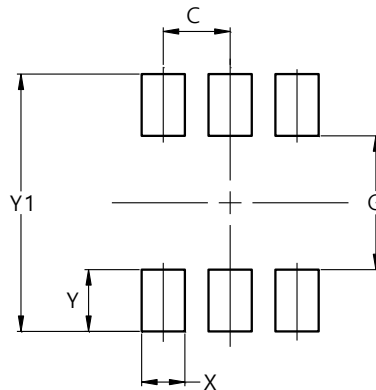


SOT363			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT363



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

IMPORTANT NOTICE

1. DIODES INCORPORATED (Diodes) AND ITS SUBSIDIARIES MAKE NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO ANY INFORMATION CONTAINED IN THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).
2. The Information contained herein is for informational purpose only and is provided only to illustrate the operation of Diodes' products described herein and application examples. Diodes does not assume any liability arising out of the application or use of this document or any product described herein. This document is intended for skilled and technically trained engineering customers and users who design with Diodes' products. Diodes' products may be used to facilitate safety-related applications; however, in all instances customers and users are responsible for (a) selecting the appropriate Diodes products for their applications, (b) evaluating the suitability of Diodes' products for their intended applications, (c) ensuring their applications, which incorporate Diodes' products, comply the applicable legal and regulatory requirements as well as safety and functional-safety related standards, and (d) ensuring they design with appropriate safeguards (including testing, validation, quality control techniques, redundancy, malfunction prevention, and appropriate treatment for aging degradation) to minimize the risks associated with their applications.
3. Diodes assumes no liability for any application-related information, support, assistance or feedback that may be provided by Diodes from time to time. Any customer or user of this document or products described herein will assume all risks and liabilities associated with such use, and will hold Diodes and all companies whose products are represented herein or on Diodes' websites, harmless against all damages and liabilities.
4. Products described herein may be covered by one or more United States, international or foreign patents and pending patent applications. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks and trademark applications. Diodes does not convey any license under any of its intellectual property rights or the rights of any third parties (including third parties whose products and services may be described in this document or on Diodes' website) under this document.
5. Diodes' products are provided subject to Diodes' Standard Terms and Conditions of Sale (<https://www.diodes.com/about/company/terms-and-conditions/terms-and-conditions-of-sales/>) or other applicable terms. This document does not alter or expand the applicable warranties provided by Diodes. Diodes does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.
6. Diodes' products and technology may not be used for or incorporated into any products or systems whose manufacture, use or sale is prohibited under any applicable laws and regulations. Should customers or users use Diodes' products in contravention of any applicable laws or regulations, or for any unintended or unauthorized application, customers and users will (a) be solely responsible for any damages, losses or penalties arising in connection therewith or as a result thereof, and (b) indemnify and hold Diodes and its representatives and agents harmless against any and all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim relating to any noncompliance with the applicable laws and regulations, as well as any unintended or unauthorized application.
7. While efforts have been made to ensure the information contained in this document is accurate, complete and current, it may contain technical inaccuracies, omissions and typographical errors. Diodes does not warrant that information contained in this document is error-free and Diodes is under no obligation to update or otherwise correct this information. Notwithstanding the foregoing, Diodes reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes.
8. Any unauthorized copying, modification, distribution, transmission, display or other use of this document (or any portion hereof) is prohibited. Diodes assumes no responsibility for any losses incurred by the customers or users or any third parties arising from any such unauthorized use.
9. This Notice may be periodically updated with the most recent version available at <https://www.diodes.com/about/company/terms-and-conditions/important-notice>

The Diodes logo is a registered trademark of Diodes Incorporated in the United States and other countries.
All other trademarks are the property of their respective owners.
© 2026 Diodes Incorporated. All Rights Reserved.

www.diodes.com